



DMP3036SFG

30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
-30V	$20m\Omega @ V_{GS} = -10V$	-30A
-300	29mΩ @ V _{GS} = -5V	-30A

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

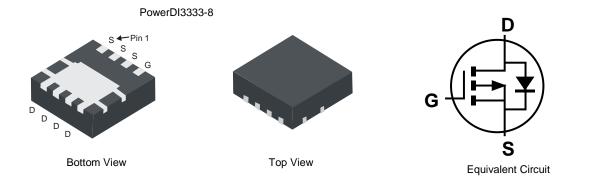
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low R_{DS(ON)} ensures on state losses are minimized.
- Small form factor thermally efficient package enables higher density end products.
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product.
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
 Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208⁽²⁾
- Weight: 0.03 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3036SFG-7	PowerDI3333-8	2,000/Tape & Reel
DMP3036SFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes: 1. N

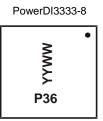
No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free.

3. Haloger- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at httphttps://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



P36 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 17 = 2017) WW = Week Code (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	-30	V	
Gate-Source Voltage	V _{GSS}	±25	V	
Continuous Drain Current (Note 6) V_{GS} = -10V	T _A = +25°C T _A = +70°C	ID	-8.7 -7.0	A
Continuous Drain Current (Note 7) $V_{GS} = -10V$	T _C = +25°C T _C = +70°C	ID	-30 -25	A
Continuous Drain Current (Note 6) $V_{GS} = -5V$	T _A = +25°C T _A = +70°C	ID	-7.2 -5.8	A
Continuous Drain Current (Note 7) $V_{GS} = -5V$ $T_C = +25^{\circ}C$ $T_C = +70^{\circ}C$		ID	-30 -24	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-80	A	
Maximum Continuous Body Diode Forward Current (Note 6)	ls	-3.6	A	
Avalanche Current (Note 7) L=0.3mH	I _{AS}	-17.5	A	
Avalanche Energy (Note 7) L=0.3mH	E _{AS}	64	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	P	137	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{ extsf{ heta}JA}$	65	°C/W
Total Power Dissipation (Note 6)		PD	2.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Р	55	°C/W
	t<10s	$R_{ extsf{ heta}JA}$	26	°C/W
Thermal Resistance, Junction to Case (Note 7)	R _θ JC	3.5	°C/W	
Operating and Storage Temperature Range		TJ. TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

			-				
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)		0		1		1	
Drain-Source Breakdown Voltage	BV _{DSS}	-30	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	-	-	-1.0	μA	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	-2.0	-2.5	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance	Deserve	-	13	20	mΩ	$V_{GS} = -10V, I_D = -8A$	
	R _{DS(ON)}	-	18.4	29	mΩ	$V_{GS} = -5V, I_D = -5A$	
Diode Forward Voltage	V _{SD}	-	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	-	1931	-	pF		
Output Capacitance	C _{oss}	-	226	-	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	-	168	-	pF	1 = 1.00012	
Gate Resistance	Rg	-	10.9	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge V _{GS} = -5V	Qg	-	8.8	-	nC		
Total Gate Charge V _{GS} = -10V	Qg	-	16.5	-	nC	Vps = -15V. lp = -10A	
Gate-Source Charge	Q _{gs}	-	2.6	-	nC	$v_{DS} = -15v, I_D = -10A$	
Gate-Drain Charge	Q _{gd}	-	3.6	-	nC		
Turn-On Delay Time	t _{D(ON)}	-	8.2	-	ns		
Turn-On Rise Time	t _R	-	14	-	ns	V _{GS} = -10V, V _{DD} = -15V,	
Turn-Off Delay Time	t _{D(OFF)}	-	65	-	ns	$R_{GEN} = 3\Omega$, $I_D = -10A$	
Turn-Off Fall Time	t _F	-	31.6	-	ns	7	
Reverse Recovery Time	t _{RR}	-	9.3	-	ns		
Reverse Recovery Charge	Q _{RR}	-	12.2	-	nC	I _F = -8A, di/dt = 500A/μs	

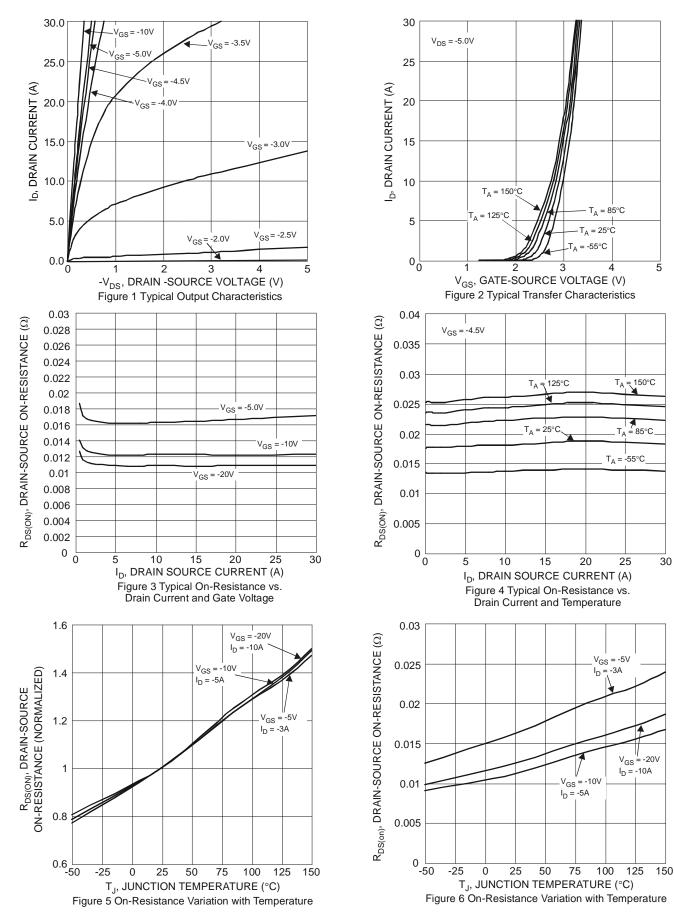
 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

7. Thermal resistance from junction to soldering point (on the exposed drain pad).

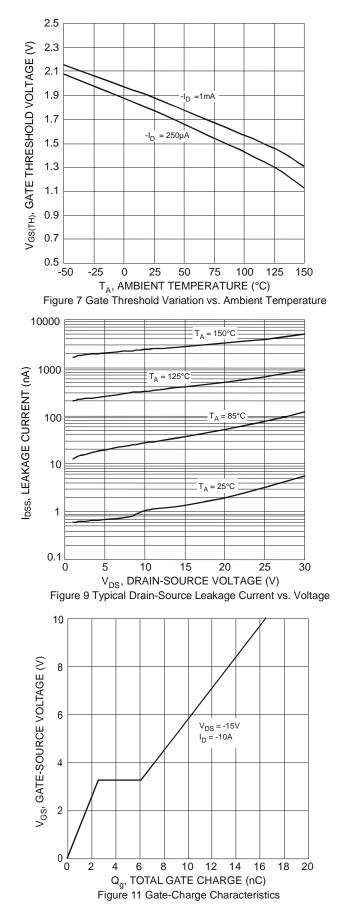
8. Short duration pulse test used to minimize self-heating effect.

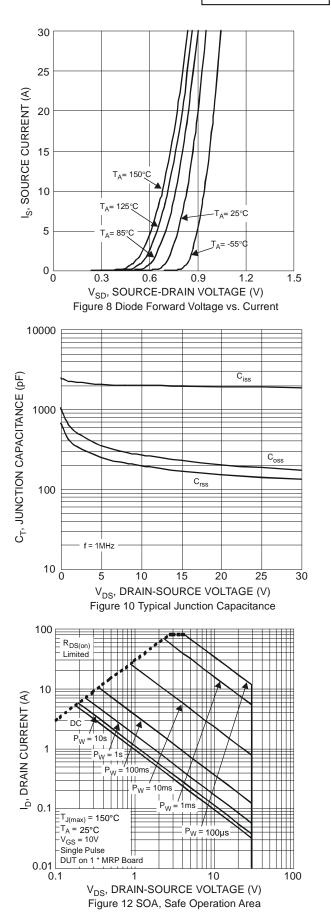
9. Guaranteed by design. Not subject to product testing.



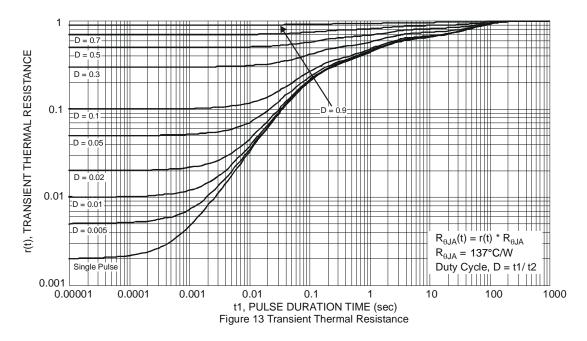








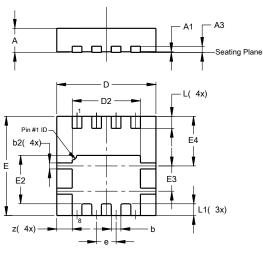






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

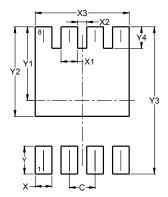


PowerDI3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A3		-	0.203			
b	0.27	0.37	0.32			
b2	0.15	0.25	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
E3	0.79	0.89	0.84			
E4	1.60	1.70	1.65			
е	-	-	0.65			
L	0.35	0.45	0.40			
L1	_	_	0.39			
z	_	_	0.515			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

PowerDI3333-8



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